

**IRF820****N-CHANNEL 500V - 2.5Ω - 4A TO-220  
PowerMesh™II MOSFET**

TYPE	V <sub>DSS</sub>	R <sub>D(on)</sub>	I <sub>D</sub>
IRF820	500 V	< 3 Ω	4 A

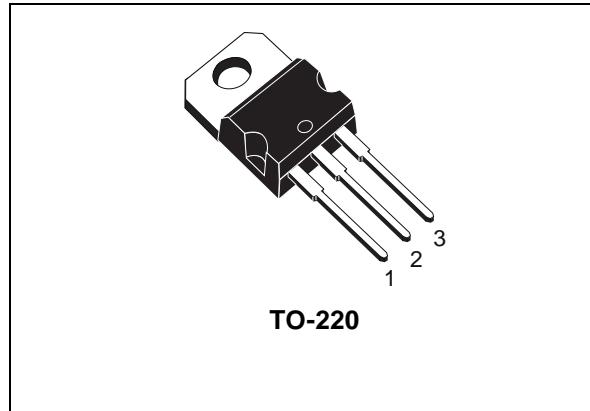
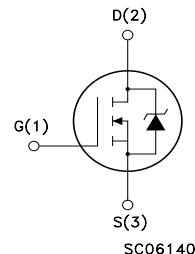
- TYPICAL R<sub>D(on)</sub> = 2.5 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

**DESCRIPTION**

The PowerMESH™II is the evolution of the first generation of MESH OVERLAY™. The layout refinements introduced greatly improve the Ron\*area figure of merit while keeping the device at the leading edge for what concerns switching speed, gate charge and ruggedness.

**APPLICATIONS**

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVES

**INTERNAL SCHEMATIC DIAGRAM****ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	500	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	500	V
V <sub>GS</sub>	Gate- source Voltage	±30	V
I <sub>D</sub>	Drain Current (continuos) at T <sub>C</sub> = 25°C	4	A
I <sub>D</sub>	Drain Current (continuos) at T <sub>C</sub> = 100°C	2.5	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	12	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	80	W
	Derating Factor	0.64	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	3.5	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C

(•)Pulse width limited by safe operating area

(1)I<sub>SD</sub> ≤ 2.5A, di/dt ≤ 50A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

## IRF820

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### THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.56	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
Rthc-sink	Thermal Resistance Case-sink Typ	0.5	°C/W
T <sub>I</sub>	Maximum Lead Temperature For Soldering Purpose	300	°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	4	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	210	mJ

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	500			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±30V			±100	nA

### ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 1.5 A		2.5	3	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , V <sub>GS</sub> = 10V	4			A

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , I <sub>D</sub> = 2A		3		S
C <sub>iss</sub>	Input Capacitance		315			pF
C <sub>oss</sub>	Output Capacitance		52			pF
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0	7.7			pF

## ELECTRICAL CHARACTERISTICS (CONTINUED)

## SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 300\text{ V}$ , $I_D = 2\text{ A}$		10		ns
$t_r$	Rise Time	$R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		13		ns
$Q_g$	Total Gate Charge	$V_{DD} = 400\text{V}$ , $I_D = 4\text{ A}$ ,		12.5		nC
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 10\text{V}$		2.7		nC
$Q_{gd}$	Gate-Drain Charge			6.1		nC

## SWITCHING OFF

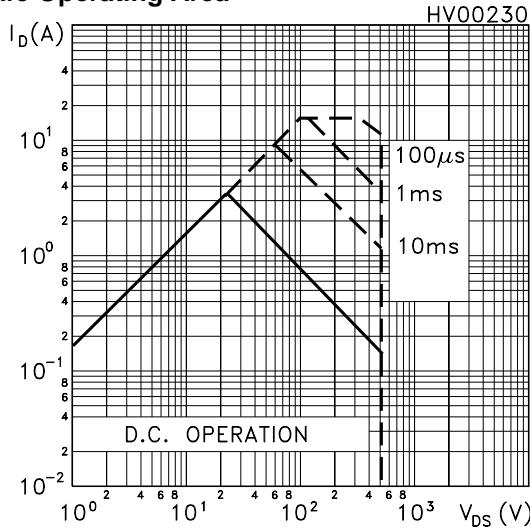
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(V_{off})}$	Off-voltage Rise Time	$V_{DD} = 400\text{V}$ , $I_D = 4\text{ A}$ ,		15		ns
$t_f$	Fall Time	$R_G = 4.7\Omega$ , $V_{GS} = 10\text{V}$		13		ns
$t_c$	Cross-over Time	(see test circuit, Figure 5)		20		ns

## SOURCE DRAIN DIODE

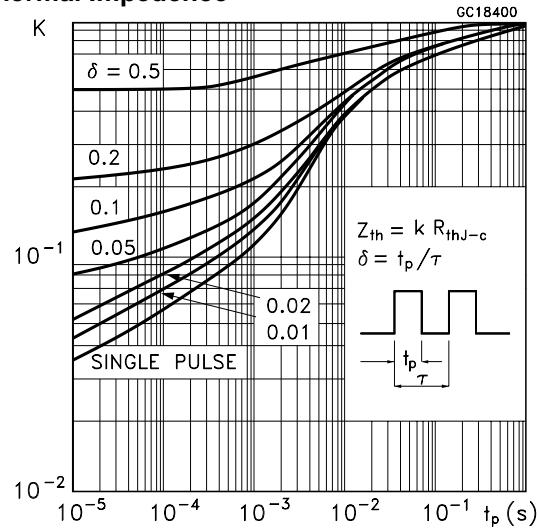
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				4	A
$I_{SDM}(2)$	Source-drain Current (pulsed)				16	A
$V_{SD}(1)$	Forward On Voltage	$I_{SD} = 4\text{ A}$ , $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 4\text{ A}$ , $dI/dt = 100\text{A}/\mu\text{s}$		400		ns
$Q_{rr}$	Reverse Recovery Charge	$V_{DD} = 100\text{V}$ , $T_j = 150^\circ\text{C}$		1.64		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current	(see test circuit, Figure 5)		8.2		A

Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

## Safe Operating Area

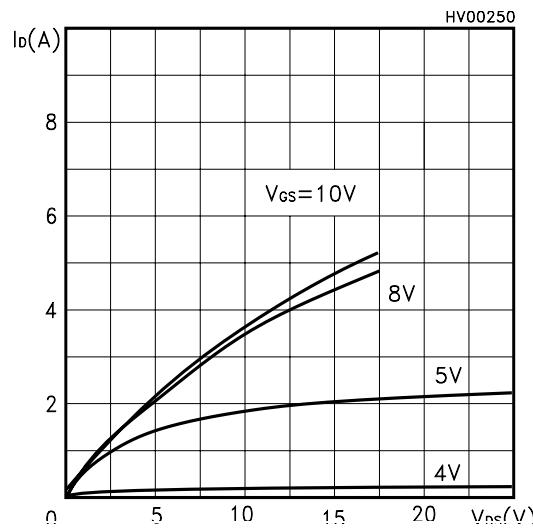


## Thermal Impedance

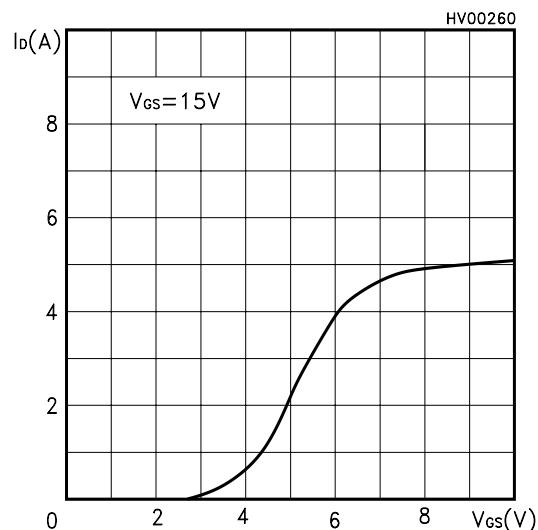


## IRF820

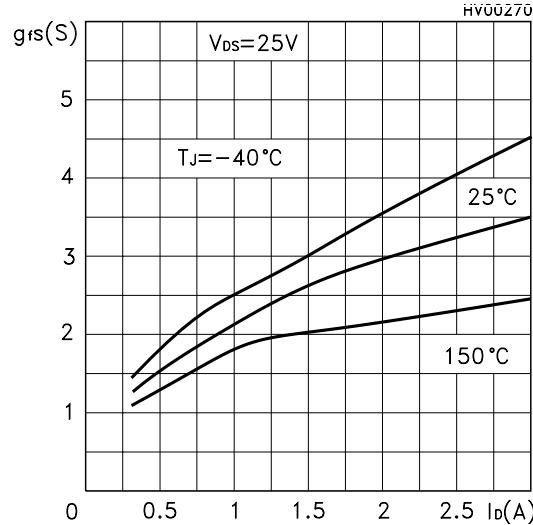
### Output Characteristics



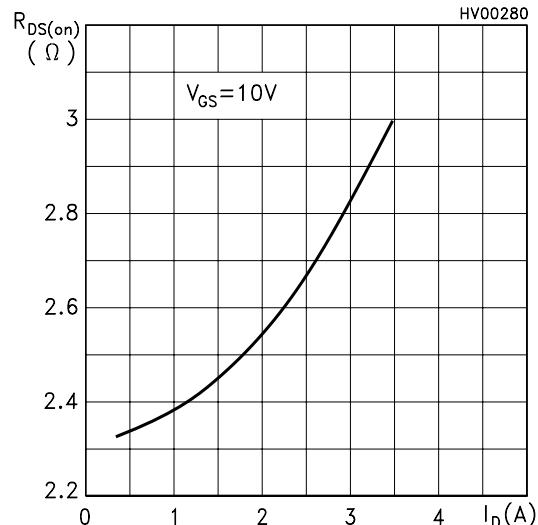
### Transfer Characteristics



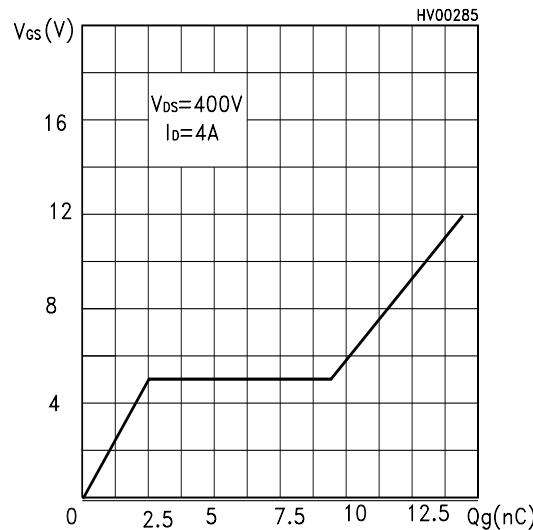
### Transconductance



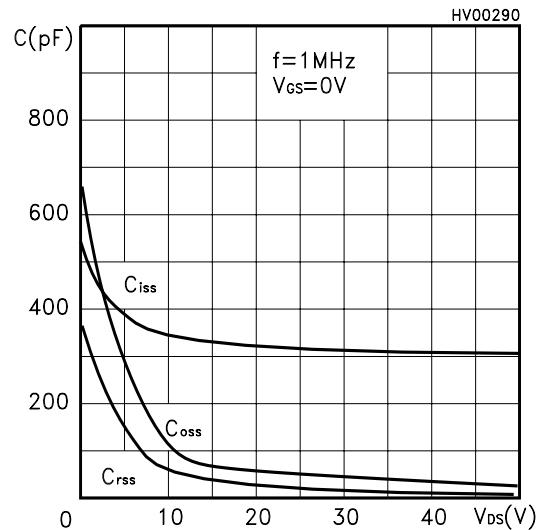
### Static Drain-source On Resistance

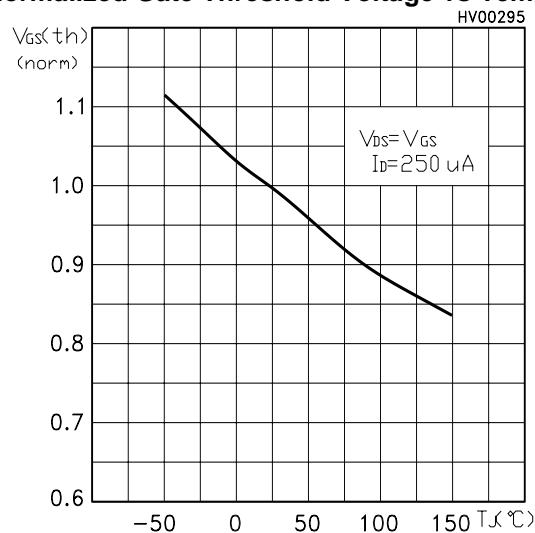
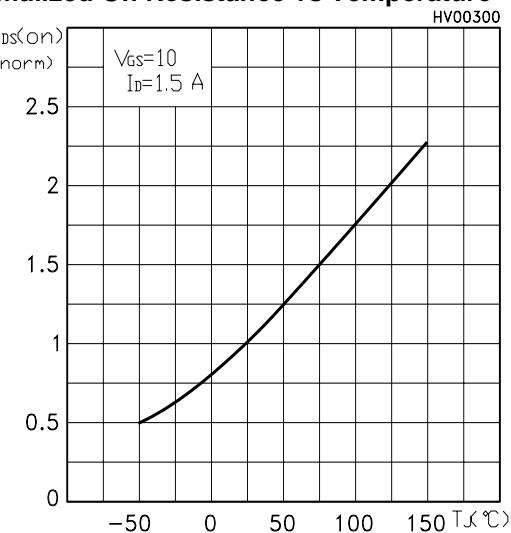
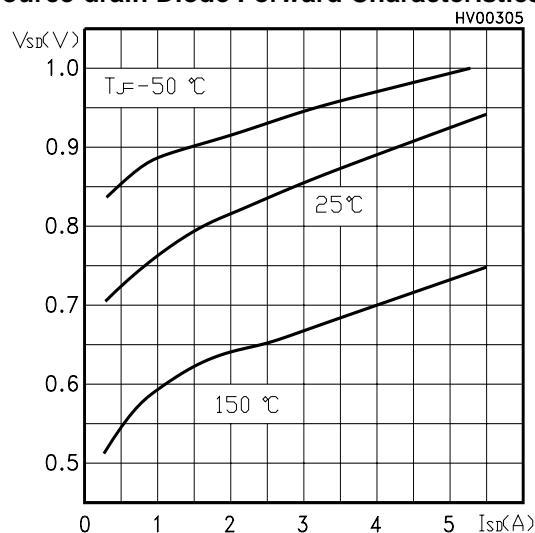


### Gate Charge vs Gate-source Voltage



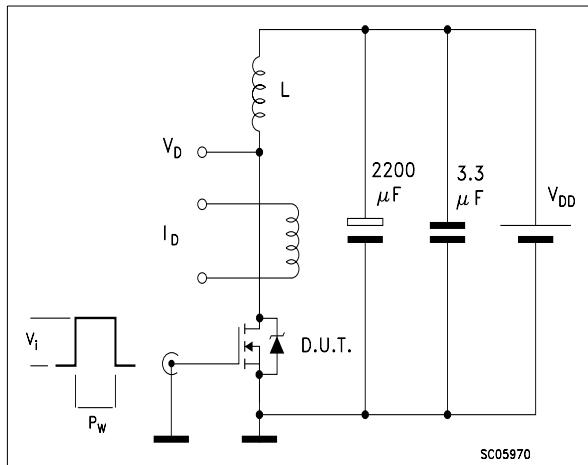
### Capacitance Variations



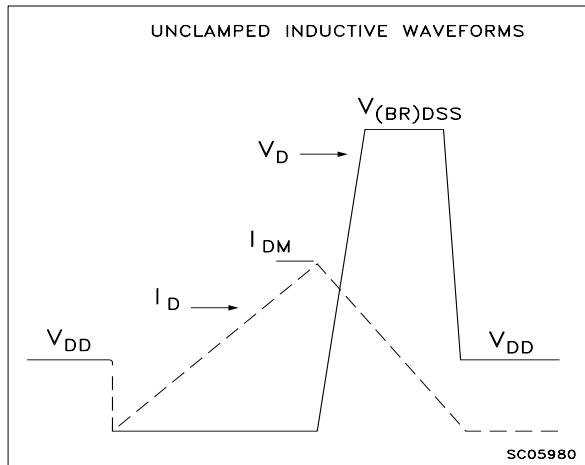
**Normalized Gate Threshold Voltage vs Temp.****Normalized On Resistance vs Temperature****Source-drain Diode Forward Characteristics**

## IRF820

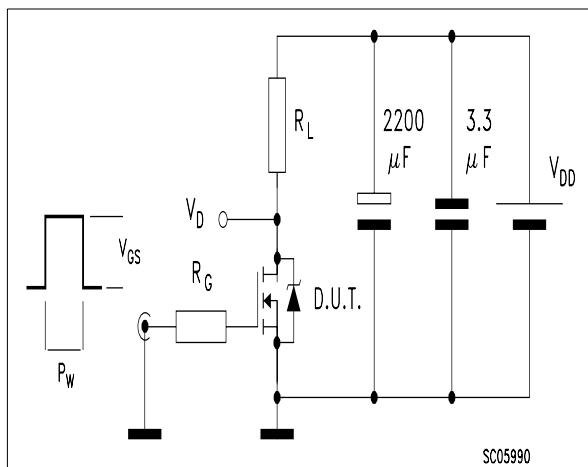
**Fig. 1:** Unclamped Inductive Load Test Circuit



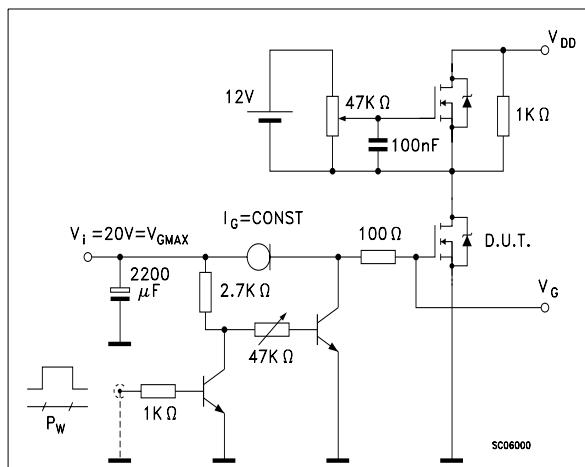
**Fig. 2:** Unclamped Inductive Waveform



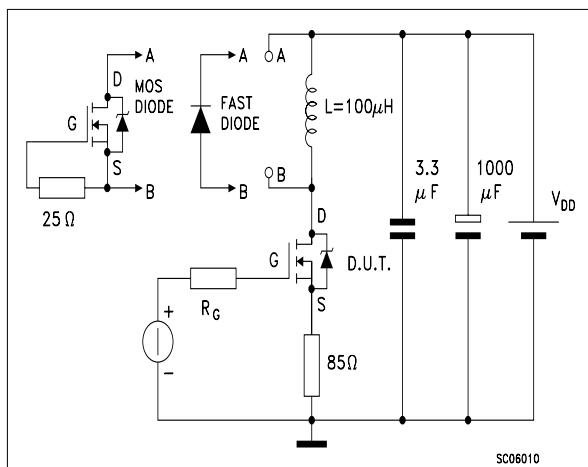
**Fig. 3:** Switching Times Test Circuit For Resistive Load



**Fig. 4:** Gate Charge test Circuit

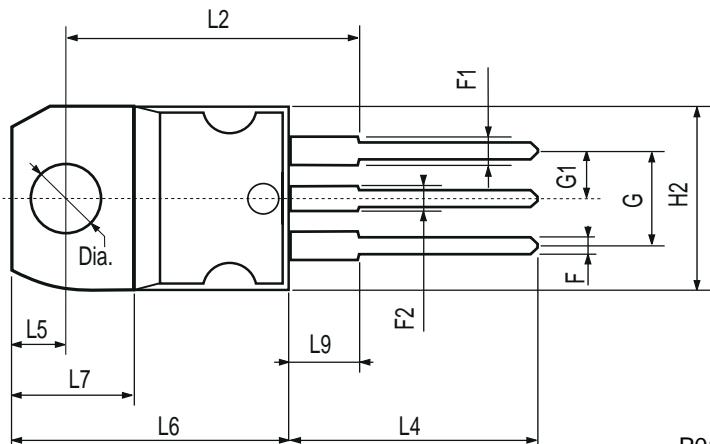
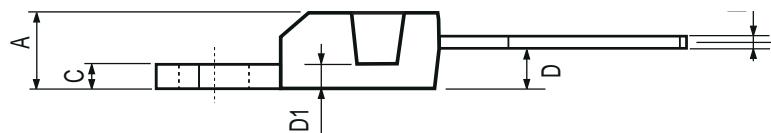


**Fig. 5:** Test Circuit For Inductive Load Switching And Diode Recovery Times



## TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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